Erratum

Determination of Carrier Density Dependent Lifetime and Quantum Efficiency in Semiconductors with a Photoluminescence Method (Application to InGaAsP/InP Heterostructures)

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Equations (B.5, 6) should read

$$\bar{\eta} = \frac{B_0}{3c^2 \bar{G}_0} \int_{x_1}^{x_2} \frac{[x - b + 3c(n_0 + p_0)] - \frac{B_1}{3cB_0} [(x - b + 3cn_0)(x - b + 3cp_0)]}{x^2 + bx - 2b^2 + 9ac} (x^2 + p) dx, \quad (\text{B.5})$$

$$I_{\sim} = \frac{\pi w^2 d \bar{G}_{\sim} B_0}{18c^2 \bar{G}_0} \int_{x_1}^{x_2} \frac{[2x - 2b + 3c(n_0 + p_0)] - \frac{B_1}{cB_0} \{(x - b)[x - b + 2c(n_0 + p_0)] + 3c^2 n_0 p_0\}}{x^2 - b^2 + 3c(a + j\omega)} (x^2 + p) dx; \quad (\text{B.6})$$